

NANOTCAD2D: Two-dimensional code for the simulation of nanoelectronic devices and structures

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Abstract

In this paper we present NANOTCAD2D, a code for the simulation of the electrical properties of semiconductor-based nanoelectronic devices and structures in two-dimensional domains. Such code is based on the solution of the Poisson/Schrödinger equation with density functional theory and of the continuity equation of the ballistic current. NANOTCAD2D can be applied to structures fabricated on III-IV, strained-silicon and silicon-germanium heterostructures, CMOS structures, and can easily be extended to new materials. In particular, in the case of SiGe heterostructures, it computes the effects of strain on the energy band profiles. The effects of interface states at the air/semiconductor interfaces, particularly significant in the case of devices obtained by selective etching, are also properly taken into account.

I. PROGRAM SUMMARY

Title of program: NANOTCAD2D

Program summary URL: <http://www.phantomshub.com>

Program available at: URL:<http://www.phantomshub.com>. (can be freely used via a web interface)

Computer on which the program has been tested: Linux PCs.

Programming Language used: FORTRAN 77.

Memory used to execute with typical data: 50-100 Mb.

Keywords: density functional theory, quantum simulation, ballistic transport, nanoscale devices, nanoelectronics, nanotechnology computer aided design.

Field of application: simulation of nanoscale semiconductor devices and structures.

Method of solution: Self-consistent solution of the Poisson-Schrödinger equation with density functional theory, in the approximation of local density, and of the continuity equation for the ballistic current with the Newton-Raphson algorithm.

Restrictions: The present simulation tool works only with rectangular grids.

II. INTRODUCTION

The electrical properties of nanoscale semiconductor devices and structures are typically determined by quantum confinement, that strongly affects the density of states of electrons and holes, and, by ballistic transport, that takes place if device length is smaller than the scattering length.

An efficient simulation tool, aimed at understanding device behavior and at designing optimized structures, must therefore include such aspects, and achieve at the same time a reasonable trade-off between efficiency and accuracy.

Here we present NANOTCAD2D, a program for the simulation of nanoelectronic semiconductor devices, based on the self-consistent solution of Poisson/Schrödinger equation and of the continuity equation for electrons and holes in the case of ballistic transport. The program allows to consider quantum confinement in one or two dimensions, and to address more complex structures that can be divided into regions in which different types of confinement are present.

NANOTCAD2D is oriented at two main classes of devices: *i*) quantum wires, i.e., structures with translation symmetry in one direction, that are completely described by the geometry of the cross section; and *ii*) ballistic field effect devices, again with translation symmetry in a direction perpendicular to that of electron motion.

Ballistic transport is simply included by assuming that the occupation factor of states injected from a given reservoir is that of the reservoir itself, i.e., obeys Fermi-Dirac distribution with the reservoir's Fermi energy.

In addition, the code implements a simplified model for localized states at the semiconductor surface exposed to air. Indeed, the depletion of a one-Dimensional or a two-Dimensional Electron Gas (1DEG or 2DEG) due to acceptor-like surface states is of primary importance in determining the electrical properties of narrow quantum wires or structures with large exposed surfaces.

At present, the code allows to consider common semiconductor materials, such as silicon, AlGaAs, InGaAs, strained silicon and silicon germanium. In the case of silicon germanium, in particular, we have developed a procedure for taking into account the effect of strain caused by different lattice constants on the band structure.

The paper has the following structure: in section III we describe the physical model implemented in the code; in section IV we discuss the numerical aspects algorithms. In section V simulation examples are presented and in section VI the conclusions. The appendix contains the user's manual.

III. PHYSICAL MODEL

The density of states for electron and holes depends on the degree of quantum confinement assumed in the different device regions. There are three possibilities: If quantum confinement is strong in both directions, the density of states is obtained by solving the two-dimensional Schrödinger equation. If quantum confinement is strong only in one direction (say, x) the density of states is written as a sum of two-dimensional subbands, the edges

of which are obtained by solving the Schrödinger equation in the x direction for each mesh point along the y axis. If confinement can be considered very weak, the density of states of the bulk material is used.

For materials with degenerate or quasi-degenerate minima in the conduction band, such as for example silicon, that has six degenerated minima, the density of states is computed with the effective mass approximation for each minimum, taking into account mass anisotropy. The same procedure is applied to degeneracy of valence band maxima.

In the following, we will discuss in some detail the expressions for the density of states and carrier density considering only one band valley, for simplicity of notation. Extension to multiple valleys is straightforward.

A. Charge density for two-dimensional quantum confinement(1DEG-1DHG)

Let us consider a region where the confinement for electrons is strong in both x and y directions. In such a case, the local density of states per unit of volume and energy near a conduction band minimum is given by:

$$N_{1D}(E, x, y) = \frac{\sqrt{2m_z}}{\pi\hbar} \times \sum_i |\Psi_i(x, y)|^2 (E - E_i)^{-\frac{1}{2}} u(E - E_i), \quad (1)$$

where $u(E - E_i)$ is the Heavyside function, Ψ_i is the solution of the Schrödinger equation in two dimensions, i.e.,

$$-\frac{\hbar^2}{2m_x} \frac{\partial^2}{\partial x^2} \Psi_i - \frac{\hbar^2}{2m_y} \frac{\partial^2}{\partial y^2} \Psi_i + E_c(x, y) \Psi_i = E_i \Psi_i, \quad (2)$$

E_i is the corresponding eigenvalue, E_c is the conduction band, m_s , $s = x, y, z$ is the effective mass in the direction denoted by the pedix, $\hbar$ is the reduced Planck's constant. At this point, by integrating the density of states multiplied by the Fermi-Dirac occupation factor, the quantum electron density can be expressed as:

$$n = \frac{\sqrt{2m_z k_B T}}{\pi\hbar} \sum_i |\Psi_i|^2 F_{-\frac{1}{2}} \left(\frac{E_f - E_i}{k_B T} \right) \quad (3)$$

where $F_{-1/2}$ is the Fermi-Dirac integral of order $-1/2$ and E_f is the Fermi energy [5].

In order to compute the hole concentration we have to solve Schrödinger equation for heavy holes and for light holes. Therefore, the conduction band in (2) is substituted by the inverted valence band $-E_v(x, y)$ and the eigenvalues $-E_i^h$, are obtained.

Therefore the hole concentration p becomes:

$$p = \frac{\sqrt{2m_z^h k_B T}}{\pi \hbar} \sum_i |\Psi_i|^2 F_{-\frac{1}{2}} \left(\frac{E_i^h - E_f}{k_B T} \right), \quad (4)$$

where m_z^h is the effective mass for holes in the z direction.

B. One-dimensional quantum confinement: two-dimensional electron or hole gas (2DEG-2DHG)

In the case of strong confinement in only one direction (for example along the x -direction), we assume that the density of states can be decomposed in a quantum term along the confined direction (x) and a semiclassical term in the other directions. The one-dimensional Schrödinger equation for electrons in the x direction for a mesh point y can be written as:

$$-\frac{\hbar^2}{2m_x} \frac{\partial^2}{\partial x^2} \Psi_i + E_c(x, y) \Psi_i = E_i(y) \Psi_i \quad (5)$$

As a consequence, the available states for electrons are grouped into two-dimensional subbands and the density of states can be expressed as follows:

$$N_{2D}(E, x, y) = \frac{\sqrt{m_y m_z}}{2\pi \hbar^2} \sum_i |\Psi_i(x, y)|^2 u(E - E_i(y)) \quad (6)$$

The electron density therefore is:

$$n = \frac{k_B T \sqrt{m_y m_z}}{\pi \hbar^2} \sum_i |\Psi_i|^2 \ln \left[1 + \exp \left(\frac{E_f - E_i}{k_B T} \right) \right] \quad (7)$$

Similar considerations apply to holes.

C. Effects of surface states

In the simulation of narrow semiconductor devices obtained with selective etching, the effects of states at the exposed surface are very important and must be taken into account in order to reproduce with accuracy the experimental results. In particular, these states can act as donors or acceptors and hence deeply affect the carrier distribution within the device.

In order to correctly model the phenomenon, we have used a simple model based on two parameters that is typically applied to metal-semiconductor contacts [6] and has been recently validated for air-semiconductor interfaces [7].

The two parameters are the density of interface states per unit energy per unit area D_S [$\text{eV}^{-1} \text{cm}^{-2}$] and the energy difference Φ^* between the vacuum level E_o and the Fermi energy that ensures a neutral charge at the interface. States with energy below $E_o - \Phi^*$ are donors and states with higher energy are acceptors.

Surface charge per unit surface can then be expressed as $Q_s = -qD_S [E_f - (E_o - \Phi^*)]$, where $-q$ is the electron charge.

D. Poisson Equation

All charge concentrations considered represent the source term of the two-dimensional Poisson equation:

$$\begin{aligned} \nabla \cdot (\epsilon \nabla \Phi) &= -\rho[\Phi] \\ &= -q [-n[\Phi] + p[\Phi] + N_D^+[\Phi] - N_A^-[\Phi] + \rho_s[\phi]] \end{aligned} \quad (8)$$

where ϵ is the dielectric constant, q is the electron charge, ρ_s is the term of surface charge per unit volume, N_D^+ and N_A^- the ionized donor and acceptor concentrations, respectively [6]. Energy bands depend on the potential as:

$$\begin{aligned} E_c(x, y) &= E_c(x, y)|_{\Phi=0} - q\Phi(x, y) \\ E_v(x, y) &= E_v(x, y)|_{\Phi=0} - q\Phi(x, y). \end{aligned} \quad (9)$$

Potential and charge density profiles in equilibrium are computed by solving the set of non linear partial differential equations described above. The case of ballistic transport is examined in the next section.

E. Ballistic transport for electrons and holes.

When carriers are injected into a semiconductor device, they are likely to be scattered by a number of possible sources, including acoustic and optical phonons, ionized impurities, defects, interfaces and other carriers. If, however, device length is smaller than the mean free path it is very likely for carriers to traverse the device without suffering scattering events. Our code includes this type of "ballistic" transport.

Ballistic transport is implemented here only in the case of one-dimensional quantum confinement, when a description in terms of two dimensional subbands is used. Indeed, we have shown that such assumption involves a negligible error also in devices with channel length of 25 nm [8].

Let us consider Figure 1, representing a subband profile for electrons along the channel. Carriers are injected into the channel from a reservoir (source) and contribute to the current only if they overcome the barrier modulated by the gate voltage and, to a lesser degree, by the drain voltage (DIBL).

If we neglect the interaction between electrons and ions and among electrons, we can simply assume that electrons with injected longitudinal energy lower than the subband maximum are reflected back to their originating contact, while the others are transmitted over the barrier and contribute to the current [9,10].

Therefore, for each subband we evaluate the subband maximum E_{imax} and the corresponding longitudinal position y_{max} . All electrons with longitudinal energy lower than E_{imax} are in equilibrium with the originating contact, while electrons with longitudinal energy higher than E_{imax} conserve the chemical potential of the injecting reservoir. The occupation

factor f is therefore:

$$f(E, E_F) = \begin{cases} \left[1 + \exp\left(\frac{E - E_{FS}}{k_B T}\right)\right]^{-1} & \text{if } y < y_{max}, \quad E < E_{imax}, \\ \left[1 + \exp\left(\frac{E - E_{FD}}{k_B T}\right)\right]^{-1} & \text{if } y > y_{max}, \quad E < E_{imax} \\ \left[1 + \exp\left(\frac{E - E_{FS}}{k_B T}\right)\right]^{-1} + \left[1 + \exp\left(\frac{E - E_{FD}}{k_B T}\right)\right]^{-1} & \text{if } E > E_{imax} \end{cases} \quad (10)$$

where E_{FS} (E_{FD}) is the source (drain) Fermi energy. If we write the total energy E as $E = E_y + E_z$, where the term $E_y = E_i + \frac{\hbar^2 k_y^2}{2m_y}$ is the longitudinal energy, and $E_z = \hbar^2 k_z^2 / 2m_z$ the transverse energy, the density of states reads:

$$N_{2D}(E_y, E_z) \, dE = 2 \sum_i |\Psi_i|^2 \frac{\sqrt{m_y m_z}}{h^2} \frac{1}{\sqrt{E_y E_z}} \, dE_y \, dE_z \quad (11)$$

and the electron density is accordingly given by:

$$n = \int_0^{E_{imax} - E_i(y)} \sum_i |\Psi_i|^2 2 \frac{\sqrt{m_y m_z}}{h^2} E_y^{-\frac{1}{2}} \, dE_y \int_0^\infty E_z^{-\frac{1}{2}} f(E, E_F) \, dE_z \quad (12)$$

The electron current is evaluated assuming that there is no tunnel current through the barrier so that only the electrons with longitudinal energy higher than E_{imax} can contribute.

$$J_n = \int_0^\infty dE_z \int_{E_{imax} - E_i(y)}^\infty \sum_i 2 \frac{\sqrt{m_y m_z}}{h^2} \frac{1}{\sqrt{E_y E_z}} \sqrt{\frac{2E_y}{m_y}} \times \left[\frac{1}{1 + \exp\left(\frac{E_y + E_z - E_{FS}}{k_B T}\right)} - \frac{1}{1 + \exp\left(\frac{E_y + E_z - E_{FD}}{k_B T}\right)} \right] dE_y \quad (13)$$

Similar considerations apply to holes.

IV. NUMERICAL ASPECTS

The flow diagram of the algorithm implemented is shown in Figure 2. The program, using an initial guess for the potential, starts with a semiclassical solution of the Poisson equation. The equation is discretized with the Box-integration method and solved with the Newton-Raphson algorithm. Dirichlet boundary conditions are enforced on each metal gate and homogeneous Neumann conditions on the rest of the domain boundary. The

solution obtained is used as an initial guess for the quantum calculation, where the nested Poisson/Schrödinger equation must be solved.

In order not to degrade convergence speed of the algorithm when also the Schrödinger equation has to be solved, we have implemented a simplified version of the predictor-corrector scheme proposed in Ref. [11]. In this way, instead of solving both equations at each Newton-Raphson step, we evaluate eigenfunctions and eigenvalues only at the beginning of a Newton-Raphson cycle: for the whole cycle eigenfunctions and the difference between the eigenvalues and the energy bands in each point of the domain are assumed to be constant. When a Newton-Raphson cycle ends the Schrödinger equation is solved again and a new cycle is started. The program ends when the difference between the two-norm of the potential at the end of two successive Newton-Raphson cycles is lower than a fixed tolerance. [12]

In Figure 3(left) a rectangular uniform mesh is shown, where it is possible to notice the subdomain $D_{i,j}$ (dashed line) associated to the generic grid point (i, j) . In our code, we have distinguished the properties of the structure in *point* characteristics and *material* characteristics.

Point characteristics are, for example, the potential, the Fermi level, charge concentrations, while material properties (e.g., energy gap, electron affinity, etc.) belong to the second group. In the figure, is also shown (solid line) the material element connected to the generic (i, j) grid point.

In each subdomain, Poisson and Schrödinger equations are discretized with box integration [13]

A. Poisson Equation

In particular, for the Poisson equation, after integrating both members over the domain $D_{i,j}$, we obtain:

$$\int \int_{D_{i,j}} \nabla \cdot (\epsilon \nabla \Phi(x, y)) dx dy = - \int \int_{D_{i,j}} \rho(x, y) dx dy, \quad (14)$$

which is discretized as

$$\begin{aligned}
& \frac{\Phi_{i+1,j} - \Phi_{i,j}}{h_i} \left[\epsilon_{i,j+1} \frac{k_j}{2} + \epsilon_{i,j} \frac{k_{j-1}}{2} \right] + \\
& \frac{\Phi_{i,j+1} - \Phi_{i,j}}{k_j} \left[\epsilon_{i,j+1} \frac{h_i}{2} + \epsilon_{i-1,j+1} \frac{h_{i-1}}{2} \right] - \\
& \frac{\Phi_{i,j} - \Phi_{i-1,j}}{h_{i-1}} \left[\epsilon_{i-1,j+1} \frac{k_j}{2} + \epsilon_{i-1,j} \frac{k_{j-1}}{2} \right] - \\
& \frac{\Phi_{i,j} - \Phi_{i,j-1}}{k_{j-1}} \left[\epsilon_{i,j} \frac{h_i}{2} + \epsilon_{i-1,j} \frac{h_{i-1}}{2} \right] = \\
& [-q(p_{i,j} - n_{i,j} + N_{Di,j}^+ - N_{Ai,j}^-) + \rho_{fi,j}] \frac{(h_i + h_{i-1})(k_j + k_{j-1})}{4}
\end{aligned} \tag{15}$$

where $h_i = x_{i+1} - x_i$, $k_j = y_{j+1} - y_j$, and pedices i, j denote the quantity in position (x_i, y_j) .

Proper boundary conditions must be enforced to the equation, such as Dirichlet boundary conditions on each metal gate and homogeneous Neumann conditions on the rest of the domain boundary. In the first case, the potential Φ is fixed, while in the second case, the electric field $\vec{\nabla}\Phi \cdot \vec{n} = -\varepsilon$ is fixed.

In the simulation code, we have chosen as reference level for energies the vacuum level E_o and hence the potential for each gate point is obtained as:

$$\Phi(i, j) = E_o - \phi_{work}^n - E_F^n \tag{16}$$

where E_F^n and ϕ_{work}^n represent the Fermi level and the work function of the n-th gate, respectively.

Let us consider a point (i, j) on the boundary and let us make reference to the Figure 3(right): observe how the region $D_{i,j}$ is much smaller with respect to the case of internal point ($D_{i,j}$ becomes a quarter in the case of each of four vertexes grid points). In this point, we enforce Neumann condition and the discretization of the Poisson equation becomes:

$$\begin{aligned}
& \varepsilon \left[\epsilon_{i,j+1} \frac{k_j}{2} + \epsilon_{i,j} \frac{k_{j-1}}{2} \right] + \\
& \frac{\Phi_{i,j+1} - \Phi_{i,j}}{k_j} \left[\epsilon_{i-1,j+1} \frac{h_{i-1}}{2} \right] - \\
& \frac{\Phi_{i,j} - \Phi_{i-1,j}}{h_{i-1}} \left[\epsilon_{i-1,j+1} \frac{k_j}{2} + \epsilon_{i-1,j} \frac{k_{j-1}}{2} \right] - \\
& \frac{\Phi_{i,j} - \Phi_{i,j-1}}{k_{j-1}} \left[\epsilon_{i-1,j} \frac{h_{i-1}}{2} \right] = \\
& [-q(p_{i,j} - n_{i,j} + N_{Di,j}^+ - N_{Ai,j}^-) + \rho_{fi,j}] \frac{(h_{i-1})(k_j + k_{j-1})}{4}
\end{aligned} \tag{17}$$

B. Schrödinger Equation

The two-dimensional single-particle Schrödinger equation for electrons, given a conduction band profile $E_c(x, y)$, reads:

$$-\frac{\hbar^2}{2} \nabla \cdot [m^{-1} \nabla \Psi_n] + E_c(x, y) \Psi_n = E_n \Psi_n \tag{18}$$

where $\Psi_n(x, y)$ represents the n -th eigenfunction, E_n is the n -th eigenenergy, m is the electron effective mass tensor in the plane perpendicular to the direction of propagation,

$$m = \begin{bmatrix} m_x & 0 \\ 0 & m_y \end{bmatrix}. \tag{19}$$

In our simulations, we have discarded the exchange-correlation term, since it provides a very small contribution. Dirichlet boundary conditions are enforced on the quantum simulation domain. [15]

With the box integration method, we obtain:

$$\begin{aligned}
& -\frac{\hbar^2}{4} \left[\frac{\Psi_{n_{i+1,j}} - \Psi_{n_{i,j}}}{h_i} \left[\frac{k_j}{m_{x_{i,j+1}}} + \frac{k_{j-1}}{m_{x_{i,j}}} \right] \right] + \\
& -\frac{\hbar^2}{4} \left[\frac{\Psi_{n_{i,j+1}} - \Psi_{n_{i,j}}}{k_j} \left[\frac{h_i}{m_{y_{i,j+1}}} + \frac{h_{i-1}}{m_{y_{i-1,j+1}}} \right] \right] + \\
& +\frac{\hbar^2}{4} \left[\frac{\Psi_{n_{i,j}} - \Psi_{n_{i-1,j}}}{h_{i-1}} \left[\frac{k_j}{m_{x_{i-1,j+1}}} + \frac{k_{j-1}}{m_{x_{i-1,j}}} \right] \right] + \\
& +\frac{\hbar^2}{4} \left[\frac{\Psi_{n_{i,j}} - \Psi_{n_{i,j-1}}}{k_{j-1}} \left[\frac{h_i}{m_{y_{i,j}}} + \frac{h_{i-1}}{m_{y_{i-1,j}}} \right] \right] + \\
E_{c_{i,j}} \Psi_{n_{i,j}} \frac{(h_i + h_{i-1})(k_j + k_{j-1})}{4} &= E_n \Psi_{n_{i,j}} \frac{(h_i + h_{i-1})(k_j + k_{j-1})}{4} \tag{20}
\end{aligned}$$

C. Numerical routines and performance

The discretized non linear Poisson equation is solved with the Newton-Raphson (NR) algorithm. The sparse system of linear algebraic equations of each NR step is solved with the package Y12MAF [14], which is based on Gaussian elimination

The eigenvalue problem resulting from the discretization of the Schrödinger equation in one dimension is solved with the routine TQLI [14], while in two dimensions is solved with the method proposed in Ref. [15] that allows to reduce computing time without significant losses in accuracy, by solving the problem in the momentum space. The method can be applied to structures with inhomogeneous effective mass and can easily be extended to the full band structure.

The computing time on an 1800 MHz Pentium IV CPU strongly depends on the type of simulation: In the case of quantum confinement in one direction the CPU running time for a 128x61 grid is 37.14 sec, while in the case of quantum confinement in two directions, with a 113x148 point grid, the CPU running time is about 95.44 sec. These results represent the worst case, with no initial guess of the unknown potential. Finally, in the case of a simulation of ballistic current the running time is strongly affected by the initial guess of the potential and is between a few minutes and an hour. The initial guess is also very important in order to avoid convergence problems of the algorithm.

V. EXAMPLES OF SIMULATION

In this section, two examples of simulations computed on nanoscale devices are shown. The first structure is a silicon-germanium high mobility electron waveguide schematically represented in Figure 4. It consists of a $\text{Si}_{0.8}\text{Ge}_{0.2}$ virtual substrate, an 11 nm strained-silicon layer in which the 1DEG forms, a 5.7 nm undoped $\text{Si}_{0.8}\text{Ge}_{0.2}$ spacer layer, a 5.7 nm $\text{Si}_{0.8}\text{Ge}_{0.2}$ doped layer, with $N_d = 10^{18} \text{ cm}^{-3}$, a 35 nm undoped $\text{Si}_{0.8}\text{Ge}_{0.2}$ spacer and a 15 nm undoped silicon cap layer. The second spacer is rather thick, in order to prevent the formation of another electron channel in the silicon cap layer. The waveguide is 160 nm wide. Finally, we assume that a triple metal gate is deposited over the structure forming a Schottky contact. For the purpose of our simulation, the Schottky junction is reverse-biased and assumed to be perfectly insulating.

Quantum confinement of carriers in the horizontal (y) direction is provided by selective etching and by the depletion region induced by acceptor states at the exposed surfaces. This last effect causes the electrical width of wire to be significantly smaller than the etched width. Along the growth (x) direction, as a consequence of the band alignment between strained-silicon and silicon-germanium, a quantum well for electrons forms. In particular, the strained silicon channel is grown under a tensile strain and thus two valleys of the conduction band, along k_x , are lowered in energy while the other four valleys are raised. This condition is required in order to obtain a confinement region for electrons. In addition, only the two lowest conduction band valleys are occupied and the energy splitting between valleys (120 meV) leads to strongly suppressed intervalley scattering.

The self-consistent Poisson/Schrödinger equation is discretized onto a nonuniform rectangular grid of 108×137 points and the electron concentration has been calculated by solving the Schrödinger equation inside the strained silicon channel. Quantum electron density is represented in Figure 5, where it is possible to observe how the electrical waveguide width is about 95 nm, instead of 160 nm, because of the electron depletion induced by interface states at the exposed surfaces. By tuning the voltage applied to the gate, it is possible to

vary the electron density in the channel and hence the number of occupied states. Thus, referring to the Landauer formula of the quantized conductance $G = N (2e^2/h)$ with N equal to the number of propagating modes, it is possible to vary, as a function of applied voltage, the quantum conductance in the channel, as shown in Figure 6.

The second simulation example refers to a “well tempered” ballistic MOSFET with channel length of 25nm, proposed by Antoniadis *et al.* [16] and schematically represented in the inset of Figure 7. The oxide thickness is 1.5 nm and the polysilicon gate has a donor concentration of $5 \times 10^{20} \text{ cm}^{-3}$. In order to reduce short channel effects a super-halo doping is implanted in the channel. The analytic doping profile can be found in Ref. [16].

Assuming fully ballistic transport within the channel, we have computed the source-to-drain current. The energy barrier that electrons encounter traveling from the source towards the drain is represented in Figure 7 for a gate voltage $V_{GS} = 1 \text{ V}$ and drain-to-source voltage $V_{DS} = 0 \text{ V}$. Only the first five subbands are shown. Quantum tunneling has not been considered in our model and therefore the transmission coefficient is unity above the peak of the barrier and zero below. Thus, only electrons with energy higher than the peak can traverse the channel without energy loss and contribute to the total current.

The transfer characteristics obtained with the MEDICI simulator and with NANOTCAD2D are compared in Figure 8.

The two-dimensional simulator is available, after registration, at the URL: <http://www.phantomshub.com>. In the directory NANOTCAD2D it is possible to find additional examples of nanoscale semiconductor devices, among which users can find two different type high mobility electron waveguides defined by selective etching on a SiGe heterostructures, a nanoscale ballistic silicon MOSFET and a nanoscale ballistic AlGaAs field effect transistor (Figure 9). The parameters of simulation can be varied according to the specific user requirements. In particular, input files can be modified by user directly via a web interface as an HTML form or uploaded from an external source (Figure 10). In the same directory it is also possible to find a detailed tutorial regarding the input data files structure.

Finally, the hub provides basic visualization capabilities for 2D and 3D plots controlled via a web interface (Figure 11).

VI. DISCUSSION AND FUTURE DEVELOPMENTS

In this paper we have presented a two dimensional quantum simulator based on the solution of the Poisson/Schrödinger equation with the Box-Integration method. The code solves also the continuity equation for electrons and holes in the case of ballistic transport, where propagating states are populated according to the occupation factor of the originating reservoir. NANOTCAD2D allows to simulate most common semiconductors, such as silicon, AlGaAs, InGaAs, strained silicon and silicon germanium and has been successfully used to simulate III-IV heterostructures, strained-silicon and silicon germanium heterostructures, CMOS structures. In the case of silicon-germanium based devices a dedicated procedure allows to take into account the effects of strain on the energy bands and on band alignment.

The code is presently being improved with full two-dimensional quantum transport and quantum tunneling, that becomes relevant for devices with channel length close to 10 nm. In addition, we are developing a model for quasi-ballistic transport, which accounts for the possibility that a fraction of carriers undergo elastic scattering, that would allow a more accurate simulation of nanoscale field effect transistor at room temperature.

FIGURES

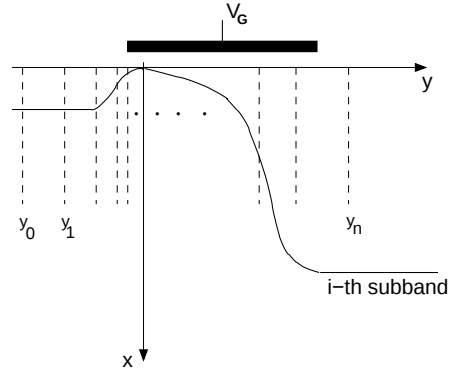


FIG. 1. Energy profile along the channel for a nanoscale FET. Only electrons with energy higher than the barrier peak contribute to the current.

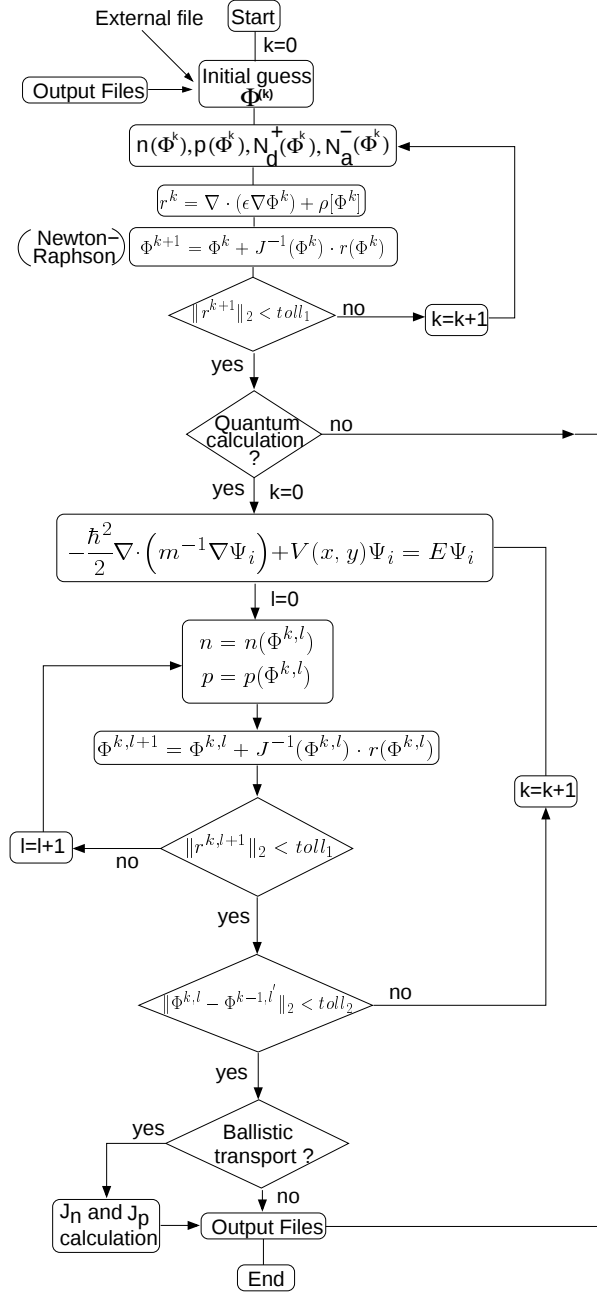


FIG. 2. Flow diagram of the algorithm implemented.

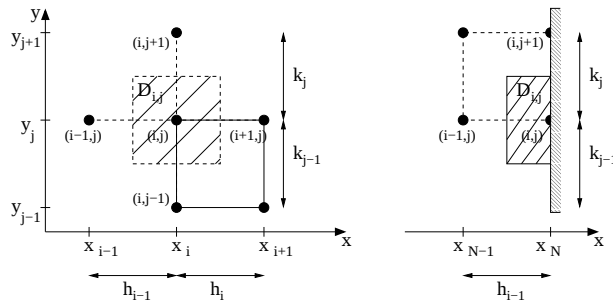


FIG. 3. $D_{i,j}$ represents the region associated to the grid point (i, j) . In figure is presented the case of an internal point (left) and a point in the edges (right).

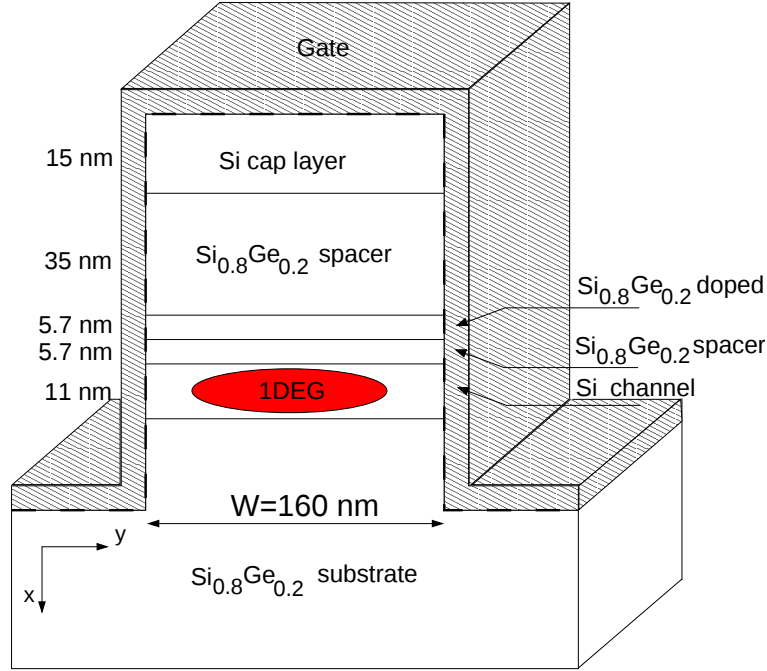


FIG. 4. Silicon-germanium electron waveguides

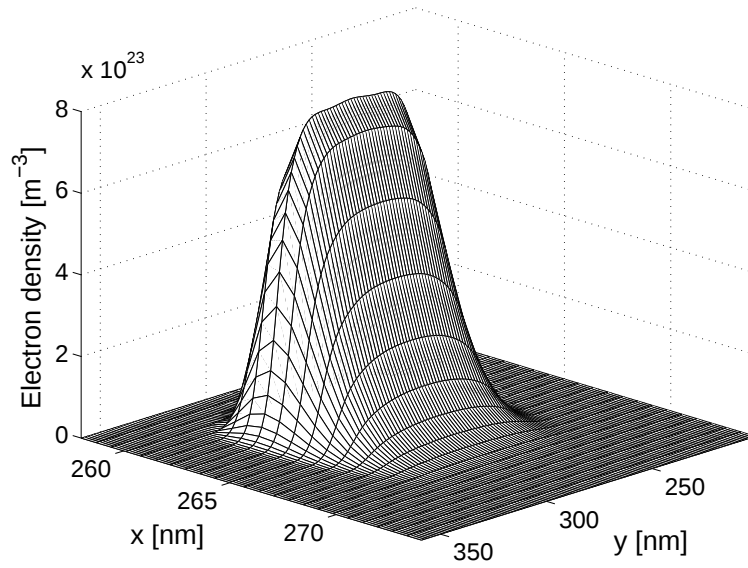


FIG. 5. Quantum electron density in the strained silicon channel.

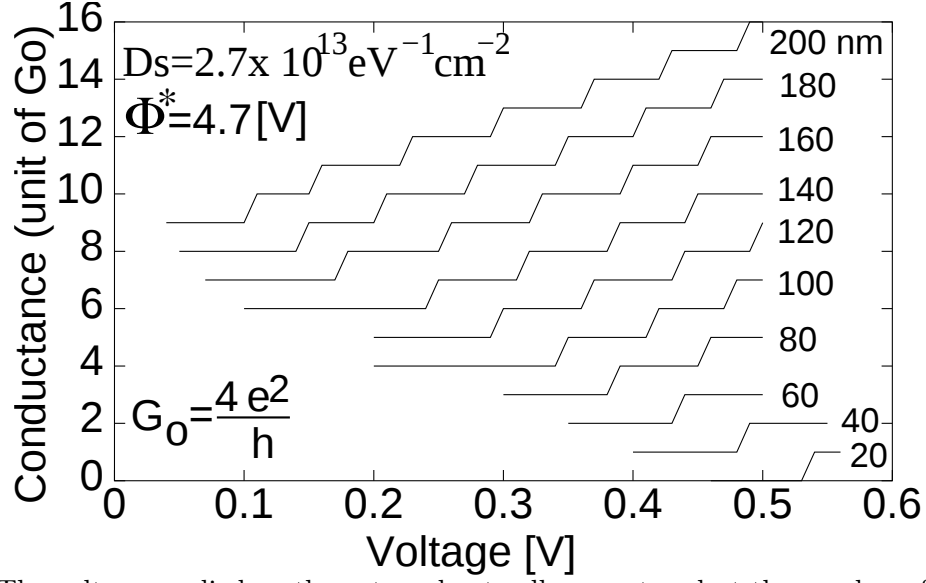


FIG. 6. The voltage applied on the external gate allows us to select the number of propagating modes in the waveguide. Hence it's possible to vary the quantized conductance in the Si channel $G = (2e^2/h)N$ as a function of gate voltage. N is the number of propagating modes. For purpose of presentation each curve is shifted by one conductance quantum.

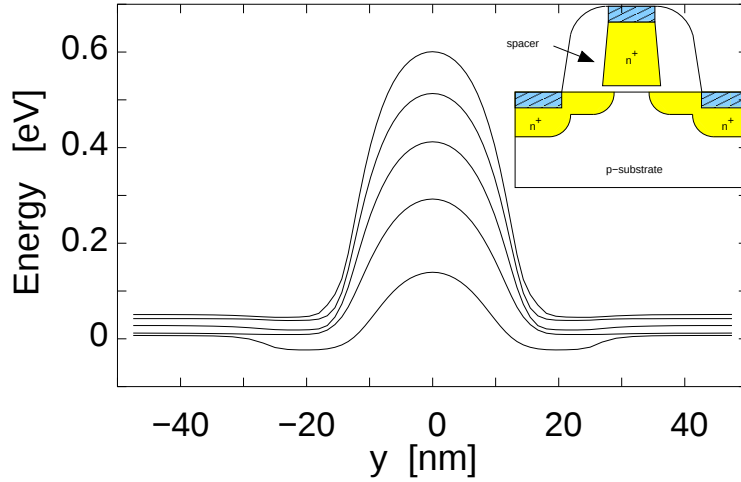


FIG. 7. Subband energies for a voltage applied to the gate of 1V. Transmission coefficient through the barrier is assumed to be unity for electrons with energy higher than the peak of the barrier and zero for electron with energy lower than the peak.

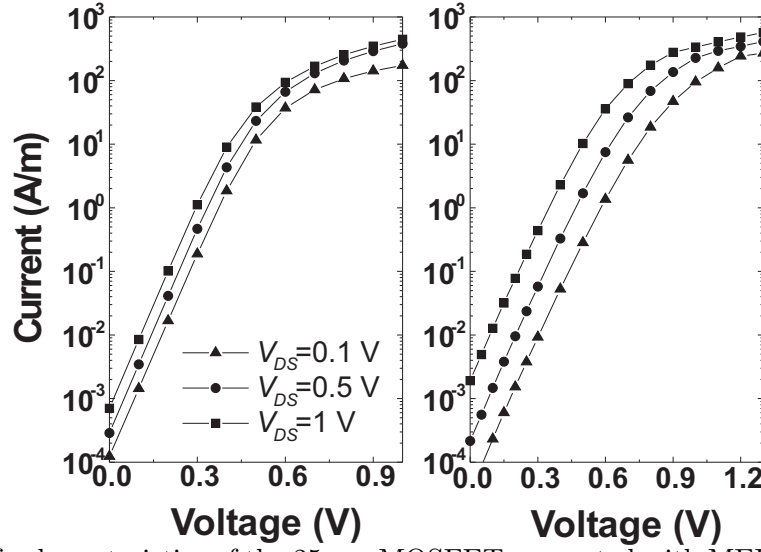


FIG. 8. Transfer characteristics of the 25 nm MOSFET computed with MEDICI (left, from Ref. Antoniadis) and with NANOTCAD2D (right).

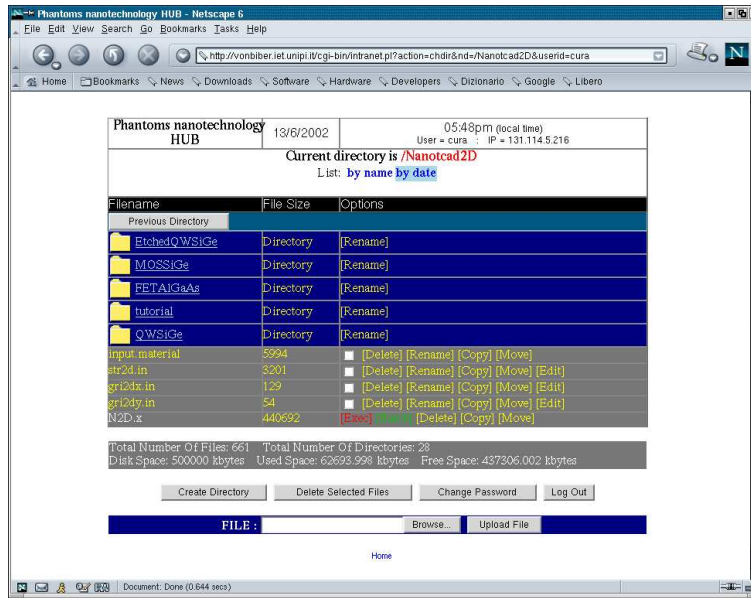


FIG. 9. Each user can use all the programs available on the HUB

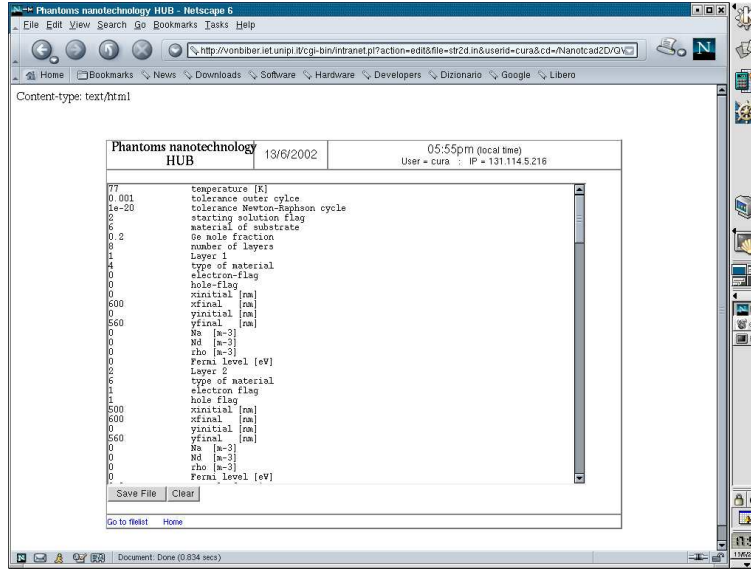


FIG. 10. The parameters of simulation can be varied in accordance with the specific user requirements.

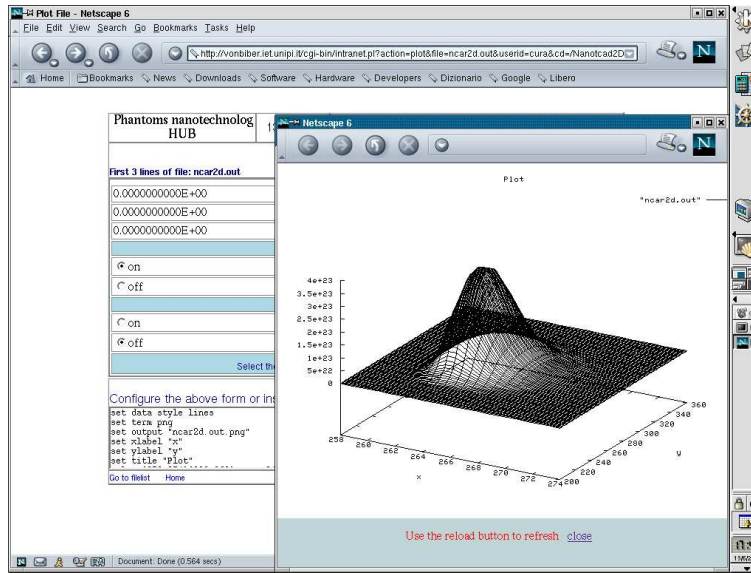


FIG. 11. The results of simulations can be graphically represented

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